

Technical Data Data Sheet N1449, Rev.- Green Products

BZT52C2V4S SERIES SURFACE MOUNT SILICON ZENER DIODES

Features:

- Planar Die Construction
- 200mW Power Dissipation
- 2.4-51V Nominal Zener Voltage
- Ideally Suited for Automated Assembly Processes
- In compliance with EU RoHS 2002/95/EC directives
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Data:

Case: SOD-323, Molded Plastic

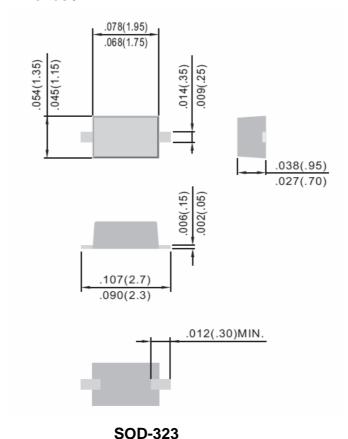
• Terminals: Solderable per MIL-STD-750, Method 2026

Polarity : Cathode Band

Weight: 0.008 grams (approx.)

Mounting Position: Any

Mechanical Dimensions: In Inches / mm



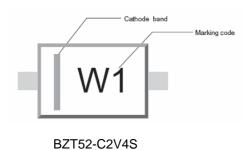
³⁰D-323

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Marking Diagram:



W1 = Marking code

Cautions: Molding resin

Epoxy resin UL: 94V-0

Ordering Information:

Device	Package	Shipping
BZT52C2V4S-BZT52C51S	SOD-323 (Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings (Ta=25°C, Unless otherwise specified)

Characteristic	Symbol	BZT52C2V4S-BZT52C51S	Unit
Power Dissipation (Note 1) @T _A = 25℃	P□	200	mW
Junction Temperature	TJ	-55 to +150	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

Note: 1 Mounted on 5.0mm 2 (.013mm thick) land areas.

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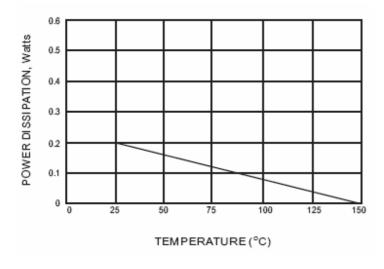
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Part Number -	Nominal Zener Voltage		Max. Zener Impedance			Max Reverse Leakage Current		Marking			
	Vz @ Izτ		Zzt @ Izt		Zzk @ Izk		Ir @ Vr		Code	Package	
	Nom. V	Min. V	Max. V	Ω	mA	Ω	mA	μА	V		
200 mWatts	Zener Did	odes									
BZT52C2V4S	2.4	2.28	2.52	85	5.0	600	1.00	100	1.0	W1	SOD-32
BZT52C2V7S	2.7	2.57	2.84	83	5.0	600	1.00	75	1.0	W2	SOD-32
BZT52C3S	3.0	2.85	3.15	95	5.0	600	1.00	50	1.0	W3	SOD-32
BZT52C3V3S	3.3	3.14	3.47	95	5.0	600	1.00	25	1.0	W4	SOD-32
BZT52C3V6S	3.6	3.42	3.78	95	5.0	600	1.00	15	1.0	W5	SOD-32
BZT52C3V9S	3.9	3.71	4.10	95	5.0	600	1.00	10	1.0	W6	SOD-32
BZT52C4V3S	4.3	4.09	4.52	95	5.0	600	1.00	5.0	1.0	W7	SOD-32
BZT52C4V7S	4.7	4.47	4.94	78	5.0	500	1.00	5.0	1.0	W8	SOD-32
BZT52C5V1S	5.1	4.85	5.36	60	5.0	480	1.00	0.1	0.8	W9	SOD-32
BZT52C5V6S	5.6	5.32	5.88	40	5.0	400	1.00	0.1	1.0	WA	SOD-32
BZT52C6V2S	6.2	5.89	6.51	10	5.0	150	1.00	0.1	2.0	WB	SOD-32
BZT52C6V8S	6.8	6.46	7.14	8	5.0	80	1.00	0.1	3.0	WC	SOD-32
BZT52C7V5S	7.5	7.13	7.88	7	5.0	80	1.00	0.1	5.0	WD	SOD-32
BZT52C8V2S	8.2	7.79	8.61	7	5.0	80	1.00	0.1	6.0	WE	SOD-32
BZT52C8V7S	8.7	8.27	9.14	7	5.0	100	1.00	0.1	6.5	87C	SOD-32
BZT52C9V1S	9.1	8.65	9.56	10	5.0	100	1.00	0.1	7.0	WF	SOD-32
BZT52C10S	10	9.50	10.50	15	5.0	150	1.00	0.1	7.5	WG	SOD-32
BZT52C11S	11	10.45	11.55	20	5.0	150	1.00	0.1	8.5	WH	SOD-32
BZT52C12S	12	11.40	12.60	20	5.0	150	1.00	0.1	9.0	WI	SOD-32
BZT52C13S	13	12.35	13.65	25	5.0	170	1.00	0.1	10.0	WK	SOD-32
BZT52C14S	14	13.30	14.70	25	5.0	170	1.00	0.1	10.5	WJ	SOD-32
BZT52C15S	15	14.25	15.75	30	5.0	200	1.00	0.1	11.0	WL	SOD-32
BZT52C16S	16	15.20	16.80	40	5.0	200	1.00	0.1	12.0	WM	SOD-32
BZT52C17S	17	16.15	17.85	40	5.0	200	1.00	0.1	13.0	17C	SOD-32
BZT52C18S	18	17.10	18.90	50	5.0	225	1.00	0.1	14.0	WN	SOD-32
BZT52C20S	20	19.00	21.00	50	5.0	225	1.00	0.1	15.0	WO	SOD-32
BZT52C22S	22	20.90	23.10	55	5.0	250	1.00	0.1	17.0	WP	SOD-32
BZT52C24S	24	22.80	25.20	80	5.0	250	1.00	0.1	18.0	WR	SOD-32
BZT52C27S	27	25.65	28.35	80	5.0	300	1.00	0.1	20.0	WS	SOD-32
BZT52C28S	28	26.60	29.40	80	5.0	300	1.00	0.1	22.0	28C	SOD-32
BZT52C30S	30	28.50	31.50	80	5.0	300	1.00	0.1	22.5	WT	SOD-32
BZT52C33S	33	31.35	34.65	80	5.0	325	1.00	0.1	25.0	WU	SOD-32
BZT52C36S	36	34.20	37.80	90	5.0	350	1.00	0.1	27.0	ww	SOD-32
BZT52C39S	39	37.05	40.95	90	5.0	350	1.00	0.1	29.0	WX	SOD-32
BZT52C43S	43	40.85	45.15	100	5.0	700	1.00	0.1	32.0	WY	SOD-32
BZT52C47S	47	44.65	49.35	100	5.0	750	1.00	0.1	35.0	WZ	SOD-32
BZT52C51S	51	48.45	53.55	100	5.0	750	1.00	0.1	38.0	XA	SOD-32

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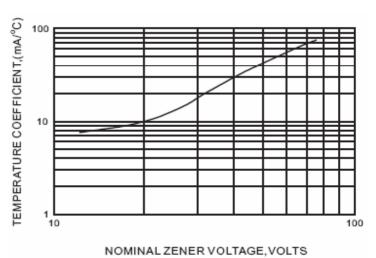
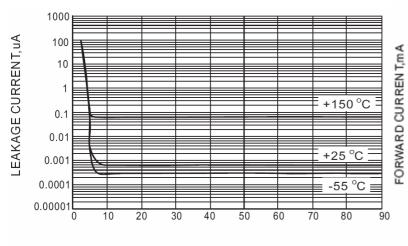


Fig.1-Steady State Power Derating

Fig.2-Temperature Coefficents



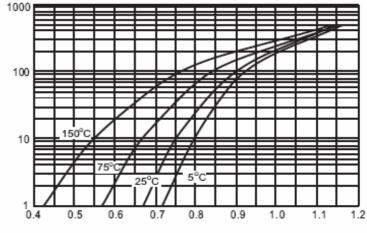


Fig.3-Typical Leakage Current

NORMAL ZENER VOLTAGE, VOLTS

Fig.4-Typical Forward Voltage

FORWARD VOLTAGE, VOLTS

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